

**In The Specification**

Please substitute the paragraph beginning at Page 7, line 17 as follows:

Fig. 6 is a schematic, cross sectional view of a bump formed according to a preferred embodiment of the present invention. The wafer 400 has a plurality of bonding pads 402 and a protection layer 406. The protection layer 406 is used to protect the surface of the wafer 400 and exposes part of the bonding pad 402 for external connection. The bonding pad 402 can be made of metals, such as aluminum. The aluminum bonding pad 402 usually has some hillocks thereon. In one preferred embodiment of the present invention, the bonding pad 402 is subject to a pretreatment by wet etching. An etchant used in the wet etching can be a peroxide such as hydrogen peroxide, hydrogen, or acids such as 60% - 80% phosphoric acid ( $H_3PO_4$ ), more than 10% nitric acid ( $HNO_3$ ), more than 10% acetic acid, or the combination thereof. The surface of the bonding pad 402 becomes planar or concave 404 after wet etching. Then, a UBM layer 408 is formed on the exposed bonding pad. A bump 410 is formed on the UBM layer 408. The bump 410 can be made of metal such as gold. Further, the bump 410 formed on either the planar surface or concave surface of the bonding pad 402 has a smooth surface.

**In The Claims**

Please add claims 12-13 as follows: